IN THE SPECIFICATION

On Page 12, please amend the paragraph starting on line 15 as follows:

The water vaporized under the temperature higher than 40°C and the alcohol has a vapor pressure higher than the processing pressure under the temperature higher than 10°C under the pressure stated above. Therefore, the alcohol is first vaporized than the water under the same temperature. The processing temperature was therefore selected to be 35°C so as not to decrease the etching rate of the silicon oxide of the sacrificial layer by not raising the temperature of the substrate. Also, the heater surrounding the entire etching chamber is maintained to have a temperature of ~~0°C~~100°C so as to discharge the gas under a vaporized state without condensing the water generated during the processing by maintaining the temperature inside of the etching chamber to be higher than that of the substrate.

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